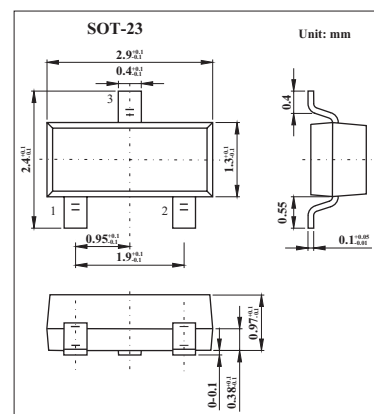


Silicon PIN Diode Array

BAR66

■ Features

- Surge protection device
- Two PIN diodes, series configuration
- Designed for surge overvoltage clamping in antiparallel connection

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	150	V
Forward current	I_F	200	mA
Forward current ($t_p = 1 \mu\text{s}$)	I_F	20	A
Power dissipation, $T_s \leq 25^\circ\text{C}^{(1)}$	P_{tot}	250	mW
Operating temperature range	T_{op}	-55 to +150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +150	$^\circ\text{C}$
Junction - ambient $^{(1)}$	R_{thJA}	≤ 450	K/W

Note

1. Package mounted on alumina $15\text{mm} \times 16.7\text{mm} \times 0.7\text{mm}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse leakage	I_R	$I_R = 5 \mu\text{A}$	150			V
Forward voltage	V_F	$I_F = 50 \text{ mA}$		0.95	1.2	V
Diode capacitance	C_T	$V_R = 35 \text{ V}, f = 1 \text{ MHz}$		0.4	0.6	pF
		$V_R = 0, f = 100 \text{ MHz}$		0.35		
Forward resistance	r_f	$I_F = 10 \text{ mA}, f = 100 \text{ MHz}$		1.5		Ω
Charge carrier life time	τ_s	$I_F = 10 \text{ mA}, I_R = 6 \text{ mA}, I_R = 3 \text{ mA}$		0.7		μs
Series inductance	L_s			2		nH

■ Marking

Marking	PMs
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